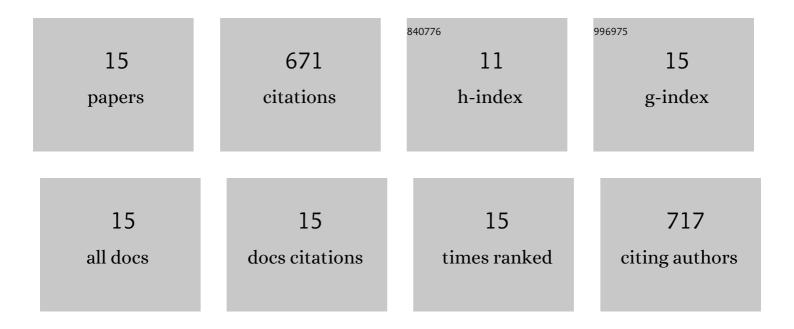
## Shihyun Ahn

List of Publications by Year in descending order

Source: https://exaly.com/author-pdf/10900012/publications.pdf Version: 2024-02-01



**SHIHVIIN ΔΗΝ** 

#	Article	IF	CITATIONS
1	Temperature-Dependent Characteristics of Ni/Au and Pt/Au Schottky Diodes on β-Ga <sub>2</sub> O <sub>3</sub> . ECS Journal of Solid State Science and Technology, 2017, 6, P68-P72.	1.8	76
2	High reverse breakdown voltage Schottky rectifiers without edge termination on Ga2O3. Applied Physics Letters, 2017, 110, .	3.3	149
3	Inductively coupled plasma etching of bulk, single-crystal Ga2O3. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2017, 35, .	1.2	32
4	High Breakdown Voltage (â^'201) \$eta \$ -Ga2O3 Schottky Rectifiers. IEEE Electron Device Letters, 2017, 38, 906-909.	3.9	159
5	Low dose <sup>60</sup> Co gamma-irradiation effects on electronic carrier transport and DC characteristics of AlGaN/GaN high-electron-mobility transistors. Radiation Effects and Defects in Solids, 2017, 172, 250-256.	1.2	26
6	Inductively coupled plasma etch damage in (-201) Ga2O3 Schottky diodes. Applied Physics Letters, 2017, 110, .	3.3	49
7	Thermal Stability of Implanted or Plasma Exposed Deuterium in Single Crystal Ga <sub>2</sub> O <sub>3</sub> . ECS Journal of Solid State Science and Technology, 2017, 6, Q3026-Q3029.	1.8	19
8	AlGaN/GaN High Electron Mobility Transistor Grown and Fabricated on ZrTi Metallic Alloy Buffer Layers. ECS Journal of Solid State Science and Technology, 2017, 6, S3078-S3080.	1.8	2
9	Extraction of Migration Energies and Role of Implant Damage on Thermal Stability of Deuterium in Ga <sub>2</sub> O <sub>3</sub> . ECS Journal of Solid State Science and Technology, 2017, 6, P794-P797.	1.8	16
10	Evaluation of AlGaN/GaN high electron mobility transistors grown on ZrTi buffer layers with sapphire substrates. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2016, 34, 051208.	1.2	4
11	Effect of front and back gates on β-Ga2O3 nano-belt field-effect transistors. Applied Physics Letters, 2016, 109, .	3.3	93
12	Deuterium incorporation and diffusivity in plasma-exposed bulk Ga2O3. Applied Physics Letters, 2016, 109, .	3.3	16
13	Effects of proton irradiation and thermal annealing on off-state step-stressed AlGaN/GaN high electron mobility transistors. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2016, 34, .	1.2	11
14	Recovery in dc and rf performance of off-state step-stressed AlGaN/GaN high electron mobility transistors with thermal annealing. Applied Physics Letters, 2015, 106, .	3.3	4
15	Characteristics of gate leakage current and breakdown voltage of AlGaN/GaN high electron mobility transistors after postprocess annealing. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2014, 32, .	1.2	15